NSN 5961-01-449-8805

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-449-8805 **Inclosure Material:** Glass **Overall Length:** Between 0.140 inches and 0.180 inches **Terminal Length:** Between 1.000 inches and 1.500 inches **Overall Diameter:** Between 0.056 inches and 0.075 inches **Function For Which Designed:** Switching **End Application:** 5865-01-346-4772 **Mounting Method: Terminal Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 100.0 breakdown voltage, dc and 75.0 working peak reverse voltage **Current Rating Per Characteristic:** 2.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Nuclear hardness critical items **Nuclear Hardness Critical Feature:** Hardened **Special Test Features:** Selected for junction capacitance of 2.0 picofards **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

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